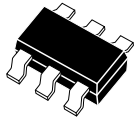


CMXD4448
SUPER-MINI
TRIPLE ISOLATED
SURFACE MOUNT
HIGH SPEED
SWITCHING DIODE



SOT-26 CASE

CentralTM
Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMXD4448 type contains three (3) Isolated High Speed Silicon Switching Diodes, manufactured by the epitaxial planar process, epoxy molded in a super-mini surface mount package, designed for applications requiring high speed switching applications. Marking code is X48.

MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$)

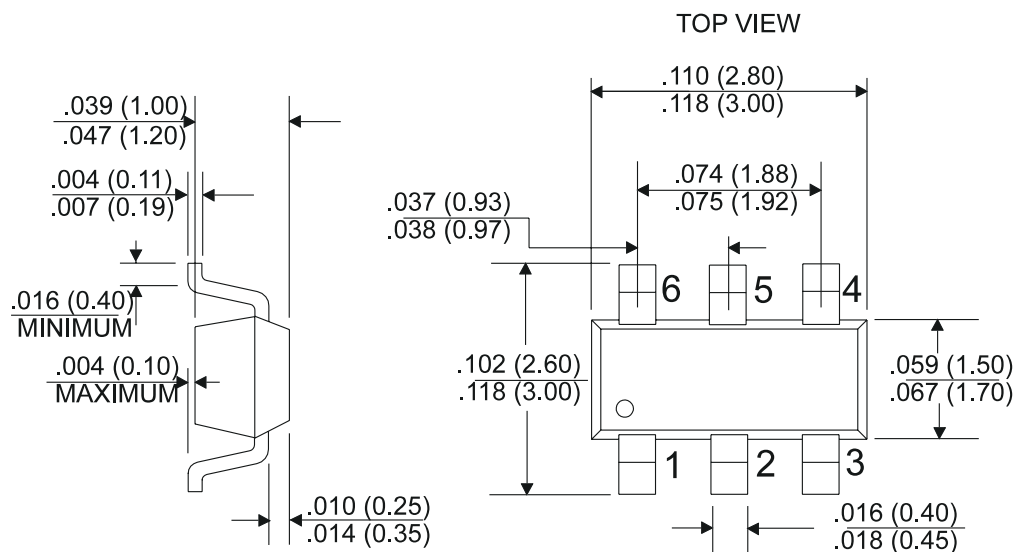
	SYMBOL		UNITS
Continuous Reverse Voltage	V_R	75	V
Peak Repetitive Reverse Voltage	V_{RRM}	100	V
Continuous Forward Current	I_F	250	mA
Peak Repetitive Forward Current	I_{FRM}	250	mA
Forward Surge Current, $t_p=1 \mu\text{sec.}$	I_{FSM}	4000	mA
Forward Surge Current, $t_p=1 \text{ sec.}$	I_{FSM}	1000	mA
Power Dissipation	P_D	350	mW
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +150	$^{\circ}\text{C}$
Thermal Resistance	Θ_{JA}	357	$^{\circ}\text{C/W}$

ELECTRICAL CHARACTERISTICS PER DIODE ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_R	$V_R=20\text{V}$		25	nA
BV_R	$I_R=5.0\mu\text{A}$	75		V
BV_R	$I_R=100\mu\text{A}$	100		V
V_F	$I_F=100\text{mA}$		1.0	V
C_T	$V_R=0, f=1 \text{ MHz}$		4.0	pF
t_{rr}	$I_R=I_F=10\text{mA}, R_L=100\Omega \text{ Rec. to } 1.0\text{mA}$		4.0	ns

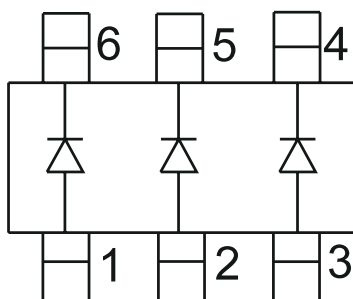
R1 (14-Sept 2000)

MECHANICAL OUTLINE - SOT-26 CASE



All Dimensions in Inches (mm)

Pin Configuration



Lead Code

- 1) Anode 1
- 2) Anode 2
- 3) Anode 3
- 4) Cathode 3
- 5) Cathode 2
- 6) Cathode 1